N-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)[a]	Q_g (Typ.)
100	0.0088 at V_{GS} = 10 V	20	18.3 nC
	0.012 at V_{GS} = 4.5 V	17	

FEATURES

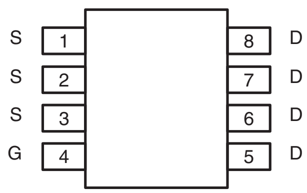
- **Halogen-free According to IEC 61249-2-21 Definition**
- TrenchFET® Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC

RoHS COMPLIANT
HALOGEN FREE

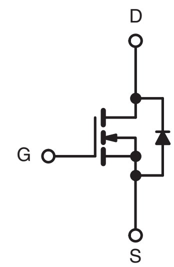
APPLICATIONS

- DC/DC Primary Side Switch
- Telecom/Server
- Industrial

SO-8



Top View



N-Channel MOSFET

Ordering Information: Si4190DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)				
Parameter		**Symbol**	**Limit**	**Unit**
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	20	A
	T_C = 70 °C		16	
	T_A = 25 °C		13.4[b, c]	
	T_A = 70 °C		10.6[b, c]	
Pulsed Drain Current		I_{DM}	70	
Continuous Source-Drain Diode Current	T_C = 25 °C	I_S	7.0	
	T_A = 25 °C		3.1[b, c]	
Single Pulse Avalanche Current	L = 0.1 mH	I_{AS}	30	
Avalanche Energy		E_{AS}	45	mJ
Maximum Power Dissipation	T_C = 25 °C	P_D	7.8	W
	T_C = 70 °C		5.0	
	T_A = 25 °C		3.5[b, c]	
	T_A = 70 °C		2.2[b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter		**Symbol**	**Typical**	**Maximum**	**Unit**
Maximum Junction-to-Ambient[b, d]	t ≤ 10 s	R_{thJA}	29	35	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	13	16	

Notes:
a. Based on T_C = 25 °C.
b. Surface mounted on 1" x 1" FR4 board.
c. t = 10 s.
d. Maximum under steady state conditions is 80 °C/W.

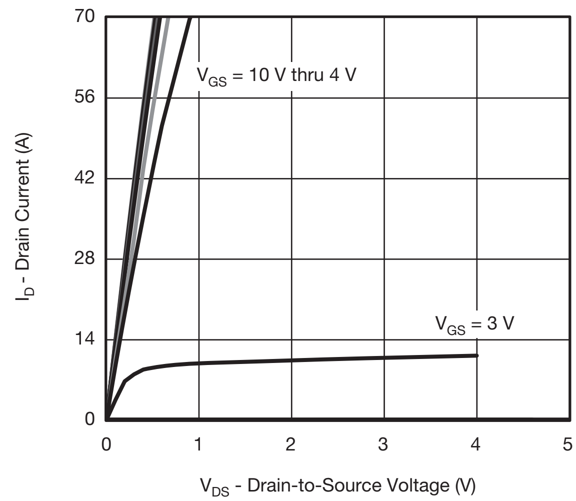
SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	100			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = 250 µA		47		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 5.8		
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS} , I_D = 250 µA	1.2		2.8	V
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 100 V, V_{GS} = 0 V			1	µA
		V_{DS} = 100 V, V_{GS} = 0 V, T_J = 55 °C			10	
On-State Drain Current[a]	$I_{D(on)}$	$V_{DS} \geq$ 5 V, V_{GS} = 10 V	30			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 15 A		0.0073	0.0088	Ω
		V_{GS} = 4.5 V, I_D = 10 A		0.0093	0.0120	
Forward Transconductance[a]	g_{fs}	V_{DS} = 15 V, I_D = 15 A		58		S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{DS} = 50 V, V_{GS} = 0 V, f = 1 MHz		2000		pF
Output Capacitance	C_{oss}			1120		
Reverse Transfer Capacitance	C_{rss}			56		
Total Gate Charge	Q_g	V_{DS} = 50 V, V_{GS} = 10 V, I_D = 10 A		38.6	58	nC
		V_{DS} = 50 V, V_{GS} = 4.5 V, I_D = 10 A		18.3	28	
Gate-Source Charge	Q_{gs}			5.4		
Gate-Drain Charge	Q_{gd}			7.3		
Gate Resistance	R_g	f = 1 MHz	0.6	2.7	5.4	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 50 V, R_L = 5 Ω $I_D \cong$ 10 A, V_{GEN} = 7.5 V, R_g = 1 Ω		12	24	ns
Rise Time	t_r			13	26	
Turn-Off Delay Time	$t_{d(off)}$			40	70	
Fall Time	t_f			11	22	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 50 V, R_L = 5 Ω $I_D \cong$ 10 A, V_{GEN} = 10 V, R_g = 1 Ω		10	20	
Rise Time	t_r			10	20	
Turn-Off Delay Time	$t_{d(off)}$			40	70	
Fall Time	t_f			11	22	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	T_C = 25 °C			7.0	A
Pulse Diode Forward Current[a]	I_{SM}				70	
Body Diode Voltage	V_{SD}	I_S = 5 A		0.75	1.1	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = 10 A, di/dt = 100 A/µs, T_J = 25 °C		51	100	ns
Body Diode Reverse Recovery Charge	Q_{rr}			51	100	nC
Reverse Recovery Fall Time	t_a			24		ns
Reverse Recovery Rise Time	t_b			27		

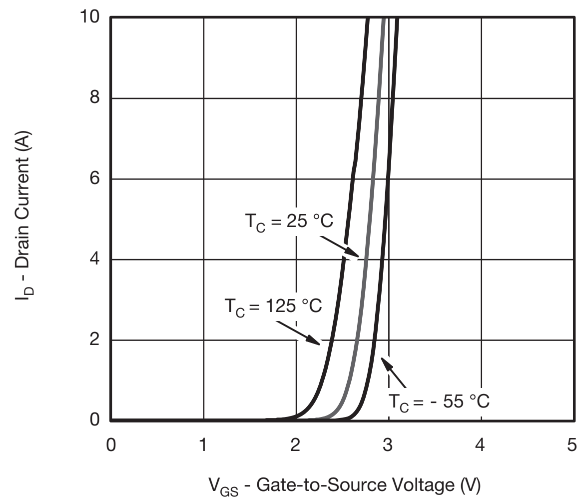
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

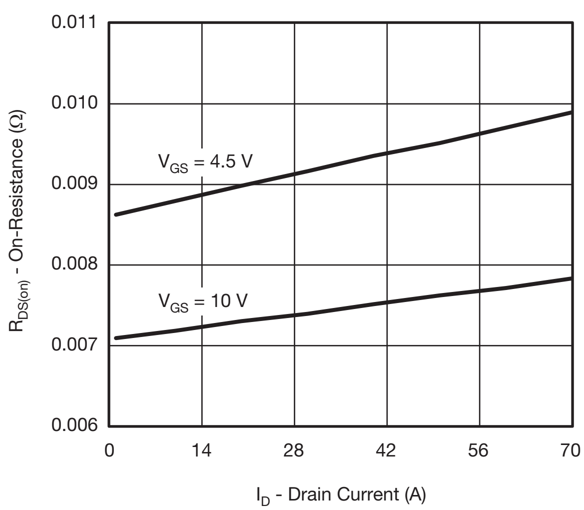
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



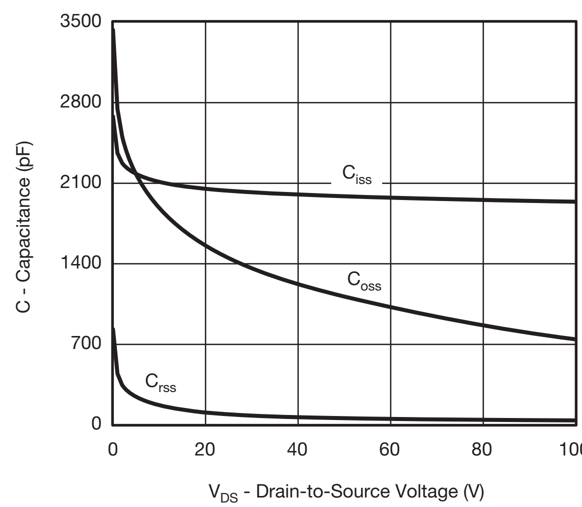
Output Characteristics



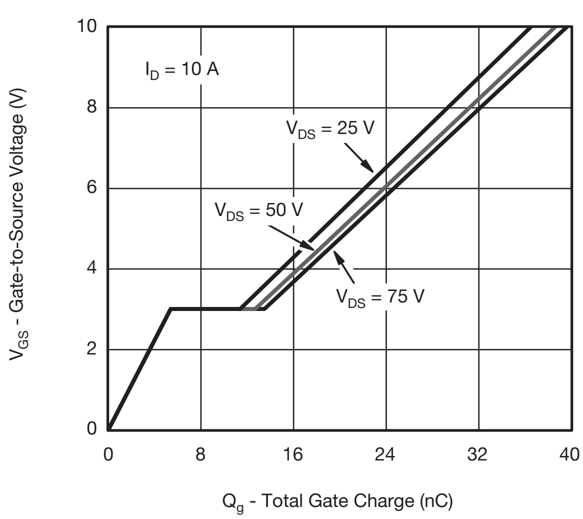
Transfer Characteristics



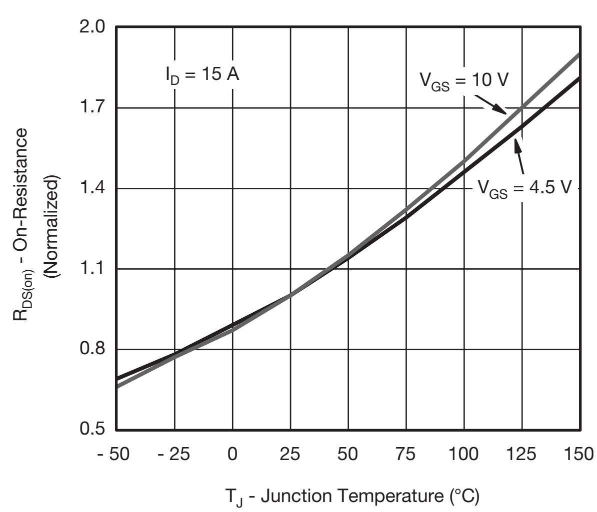
On-Resistance vs. Drain Current



Capacitance

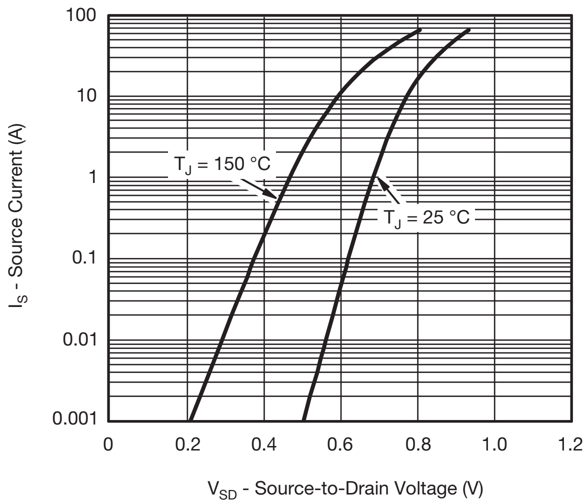


Gate Charge

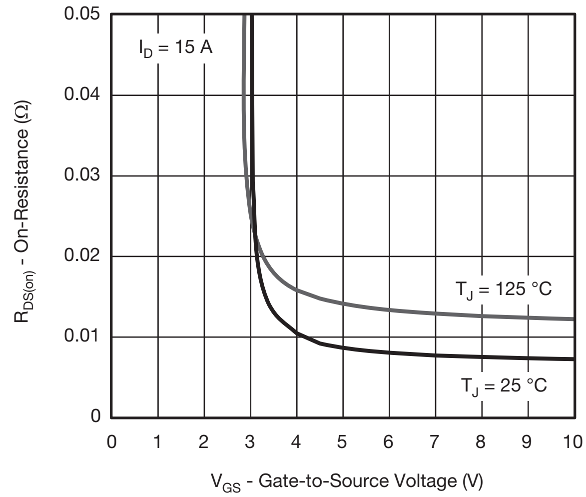


On-Resistance vs. Junction Temperature

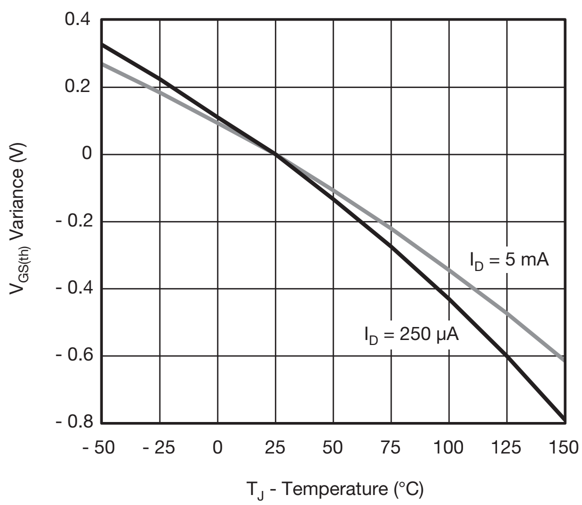
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



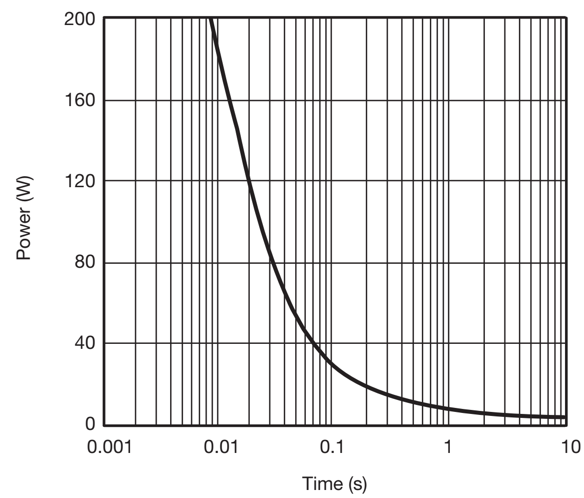
Source-Drain Diode Forward Voltage



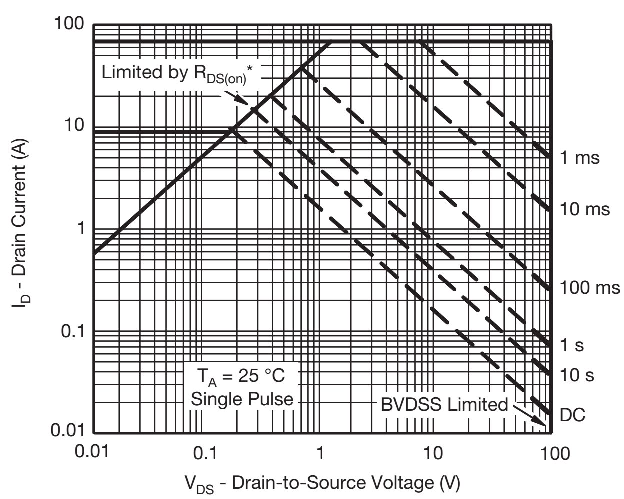
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



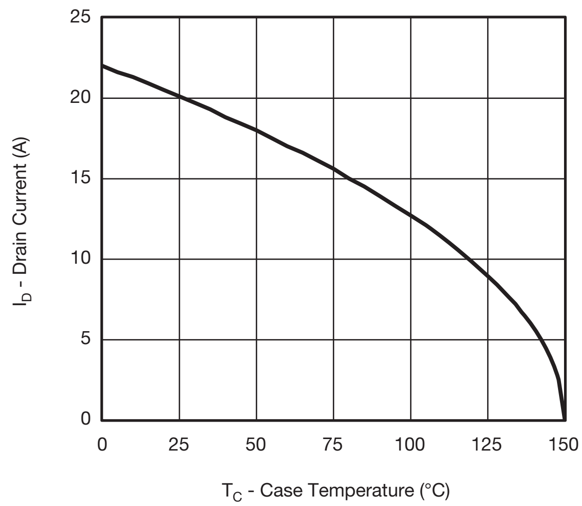
Single Pulse Power, Junction-to-Ambient



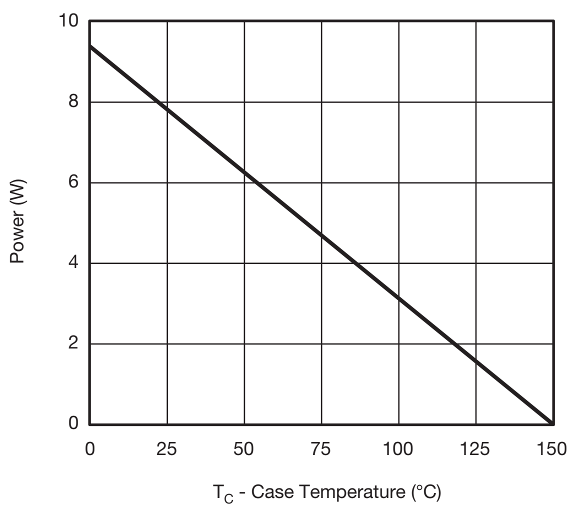
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

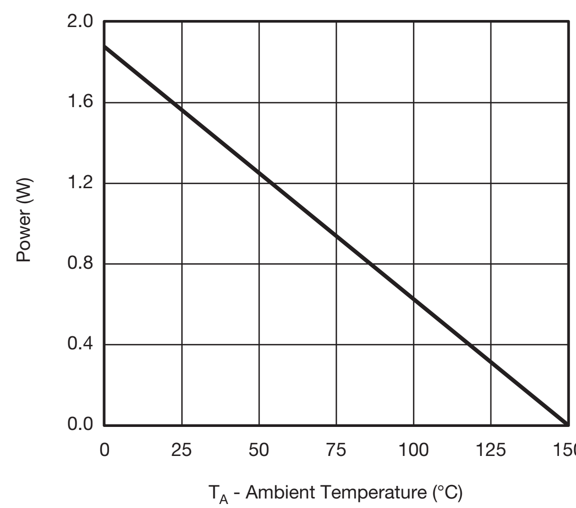
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*



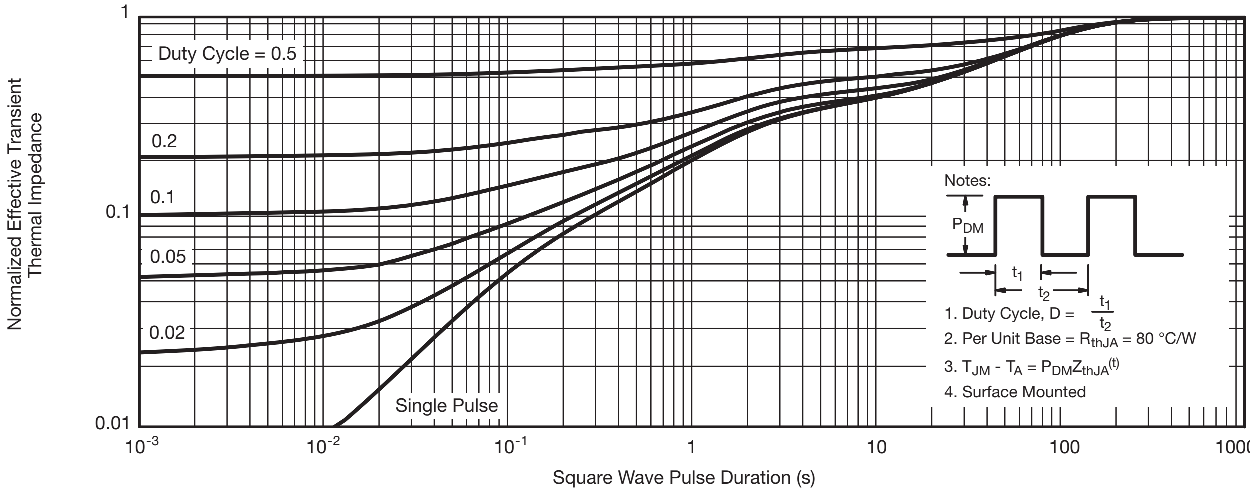
Power, Junction-to-Foot



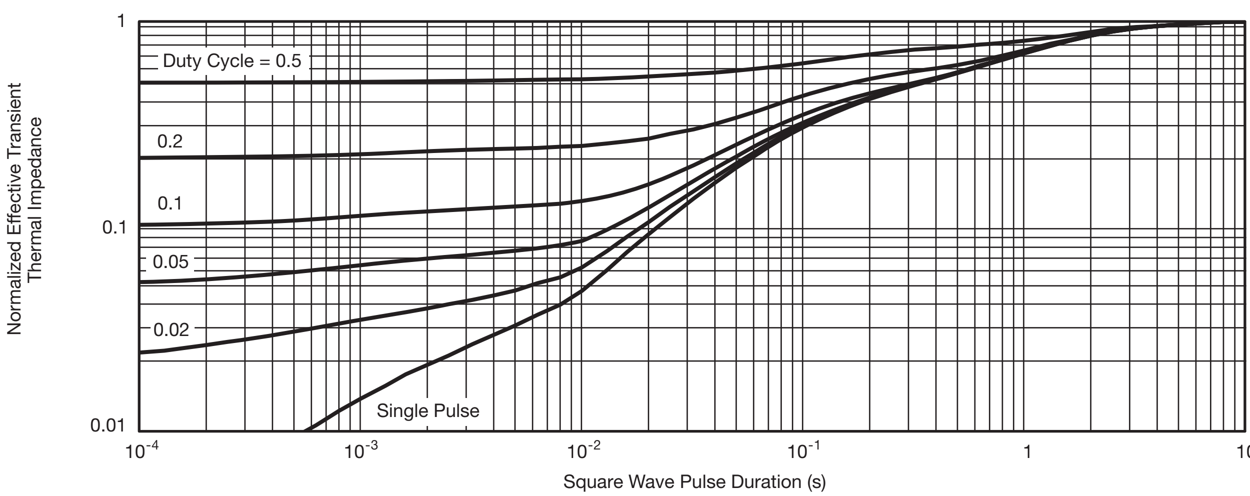
Power, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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